

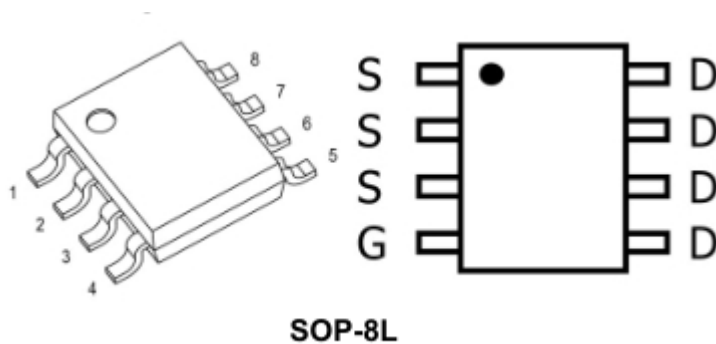
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	7.5m Ω @10V	10.3A
	9m Ω @4.5V	

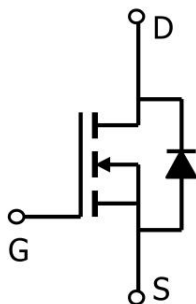
Feature

- $V_{DS} = 30V, I_D = 10.3A$
 $R_{DS(ON)} < 9m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 14m\Omega @ V_{GS} = 4.5V$
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed

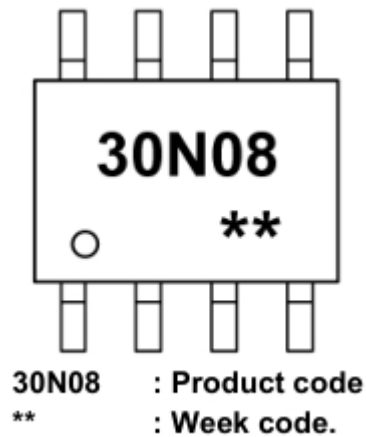
Package



Circuit diagram



Marking



Absolute maximum ratings

(T_a=25°C unless otherwise noted)

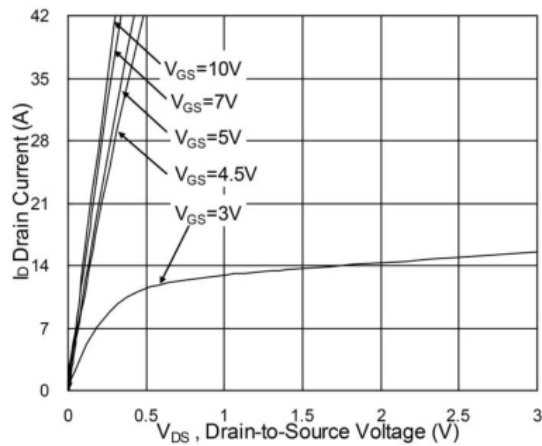
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	10.3	A
Pulsed Drain Current	I _{DM}	42	A
Maximum Power Dissipation(T _c =25°C)	P _D	1.5	W
Thermal Resistance,Junction-to-Case	R _{θJC}	85	°C/W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 150	°C

Electrical characteristics

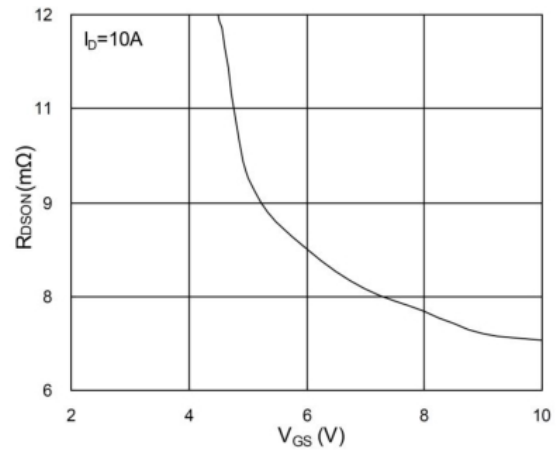
(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V _{GS} = 0V, I _D =250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} = 0V			1	uA
Gate-Source Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	uA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.2	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =8A		7.5	9	mΩ
		V _{GS} =4.5V, I _D =6A		9	14	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1.0MHz		1317		pF
Output Capacitance	C _{OSS}			163		
Reverse Transfer Capacitance	C _{rss}			131		
Switching Characteristics						
Turn-on Delay Time	T _{d(on)}	V _{GS} =10V, V _{DS} =15V, I _D =10A, R _G =3.3Ω		6.2		nS
Turn-on Rise Time	T _r			59		
Turn-off Delay Time	T _{d(off)}			27.6		
Turn-off Fall Time	T _f			8.4		
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =25V, I _D =12A		12.6		pF
Gate-Source Charge	Q _{gs}			4.2		
Gate-Drain Charge	Q _{gd}			5.1		
Source-Drain Diode Characteristics						
Gate-Drain Charge	V _{SD}	I _S =1A, V _{GS} = 0V			1.2	V

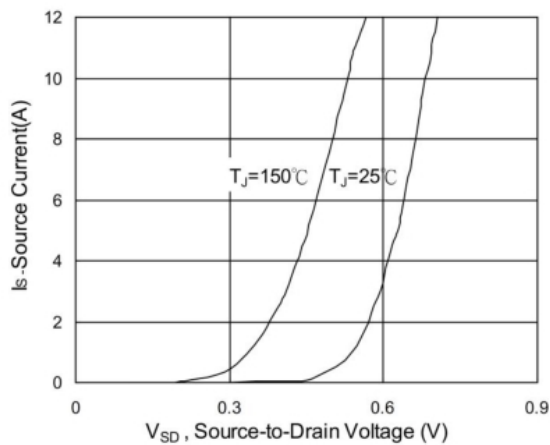
Typical Characteristics



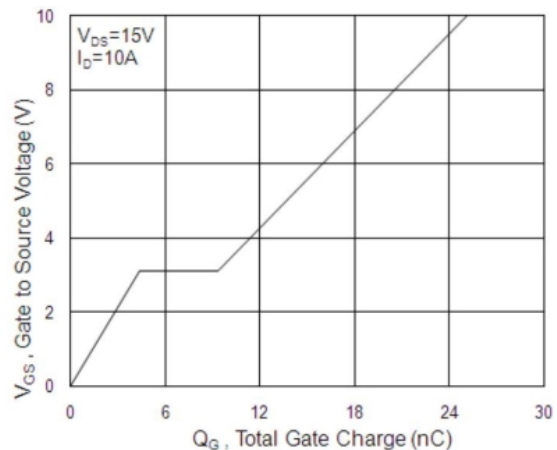
Typical Output Characteristics



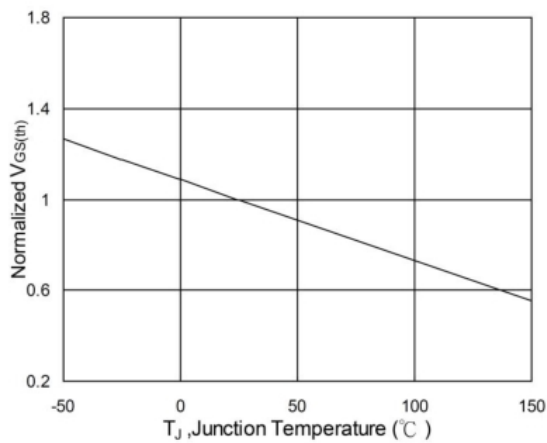
On-Resistance vs. Gate-Source



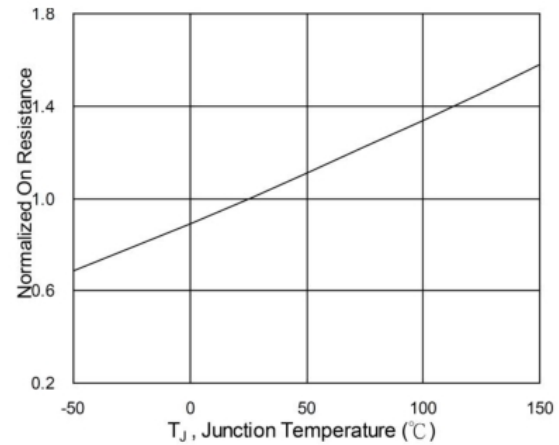
Forward Characteristics of reverse



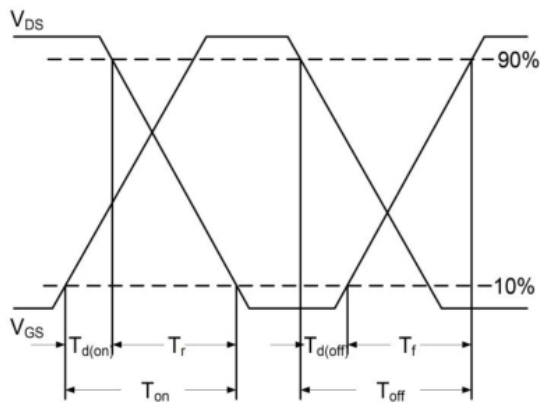
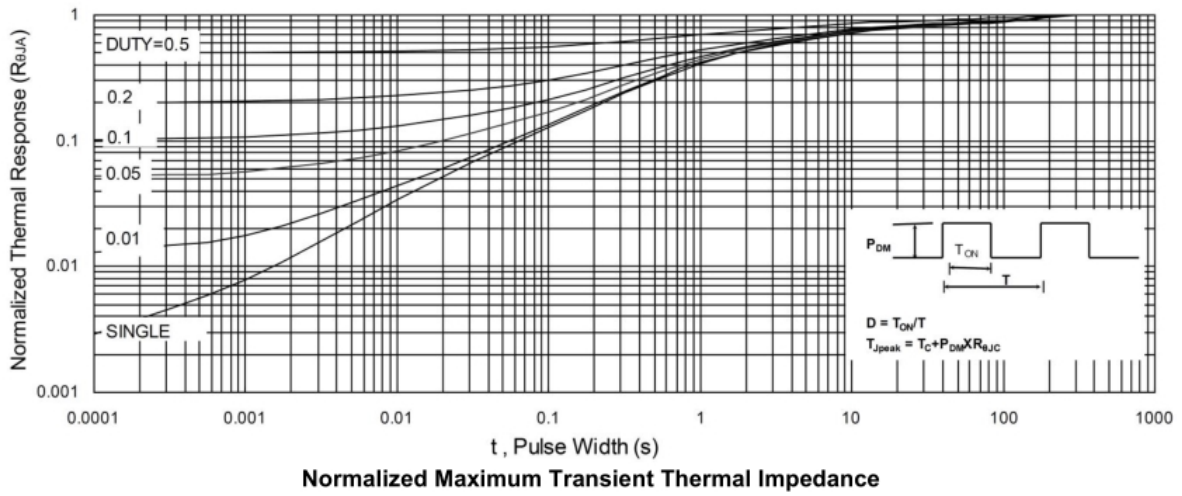
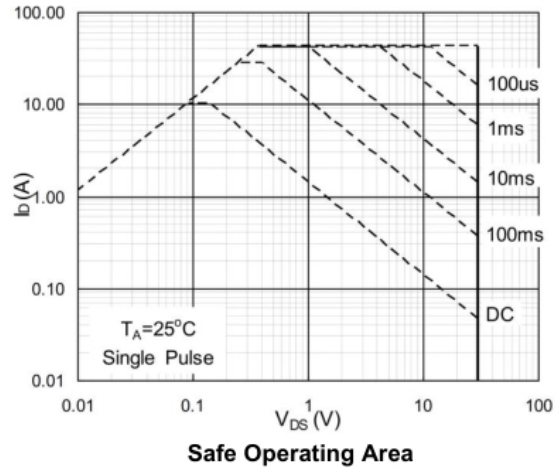
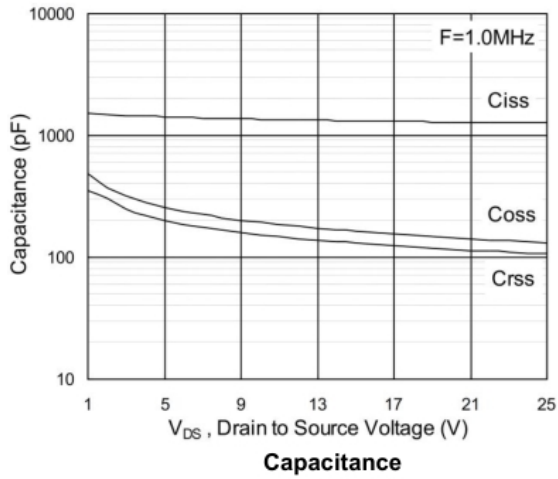
Gate-Charge Characteristics



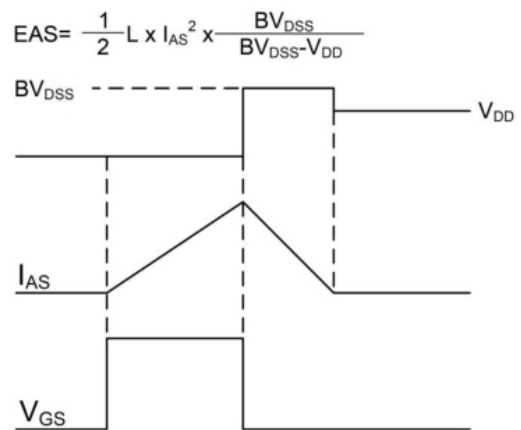
Normalized $V_{GS(th)}$ vs. T_J



Normalized $R_{DS(on)}$ vs. T_J

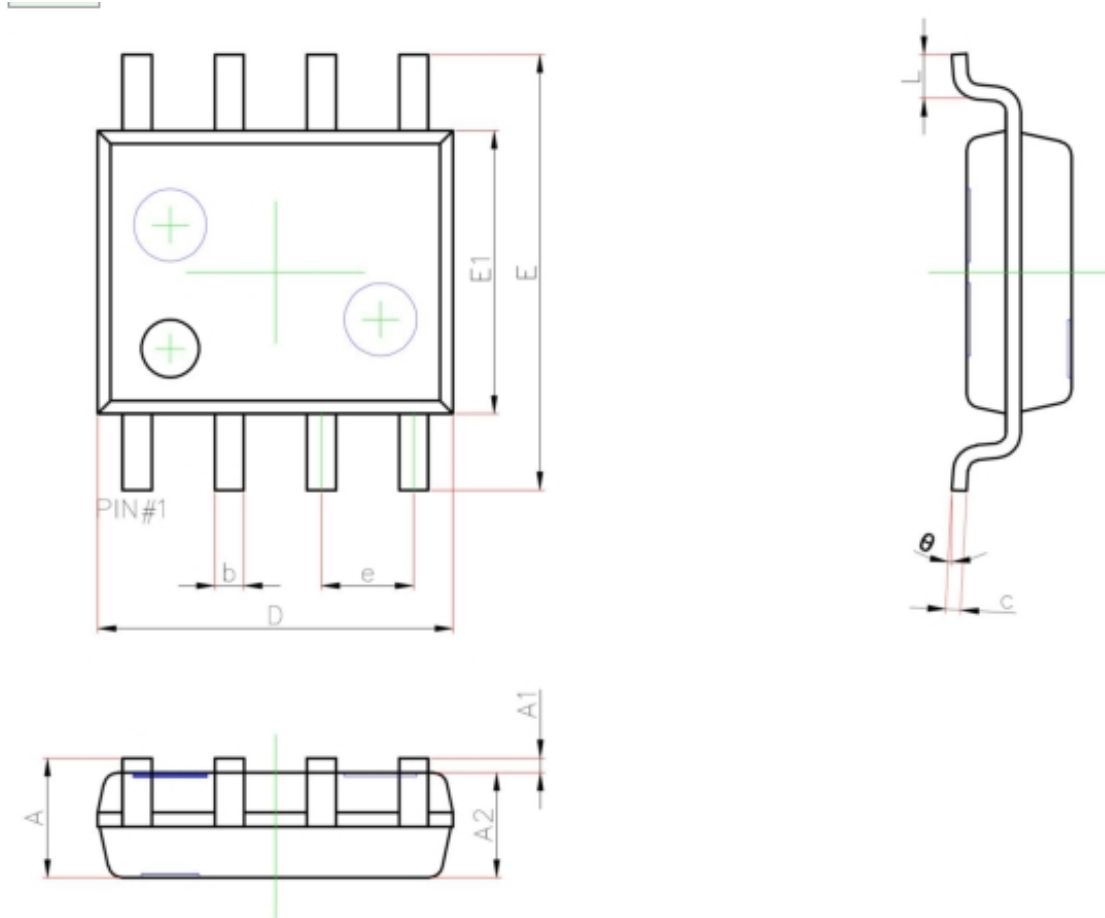


Switching Time Waveform



Unclamped Inductive Switching Waveform

SOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°